2N7000/7002, VQ1000J/P, BS170

N-Channel Enhancement-Mode MOSFET Transistors

Product Summary

Part Number	$V_{(BR)DSS}$ Min (V)	$r_{DS(on)}$ Max (Ω)	$V_{GS(th)}$ (V)	I_D (A)
2N7000	60	5 @ V_{GS} = 10 V	0.8 to 3	0.2
2N7002		7.5 @ V_{GS} = 10 V	1 to 2.5	0.115
VQ1000J		5.5 @ V_{GS} = 10 V	0.8 to 2.5	0.225
VQ1000P		5.5 @ V_{GS} = 10 V	0.8 to 2.5	0.225
BS170		5 @ V_{GS} = 10 V	0.8 to 3	0.5

Features

- Low On-Resistance: 2.5 Ω
- Low Threshold: 2.1 V
- Low Input Capacitance: 22 pF
- Fast Switching Speed: 7 ns
- Low Input and Output Leakage

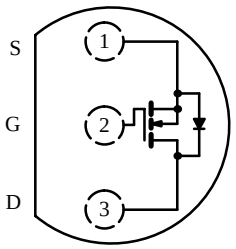
Benefits

- Low Offset Voltage
- Low-Voltage Operation
- Easily Driven Without Buffer
- High-Speed Circuits
- Low Error Voltage

Applications

- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays

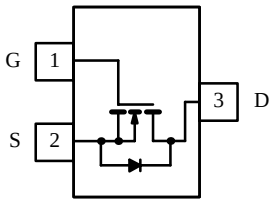
TO-226AA
(TO-92)



Top View

2N7000

TO-236
(SOT-23)

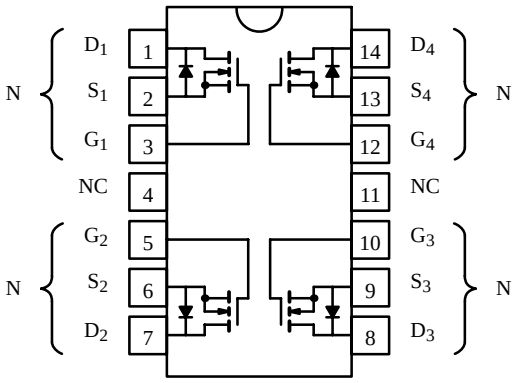


Top View

2N7002 (72)*

*Marking Code for TO-236

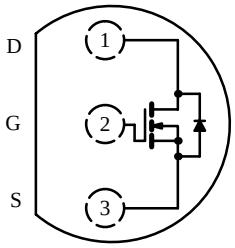
Dual-In-Line



Top View

Plastic: VQ1000J
Sidebraze: VQ1000P

TO-92-18RM
(TO-18 Lead Form)



Top View

BS170

Updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #70226.

Absolute Maximum Ratings (T_A = 25°C Unless Otherwise Noted)

Parameter		Symbol	2N7000	2N7002	Single		Total Quad	BS170	Unit
					VQ1000J	VQ1000P	VQ1000J/P		
Drain-Source Voltage		V_{DS}	60	60	60	60		60	V
Gate-Source Voltage—Non-Repetitive		V_{GSM}	±40	±40	±30			±25	
Gate-Source Voltage—Continuous		V_{GS}	±20	±20	±20	±20		±20	
Continuous Drain Current (T_J = 150°C)	T_A= 25°C	I_D	0.2	0.115	0.225	0.225		0.5	A
	T_A= 100°C		0.13	0.073	0.14	0.14		0.175	
Pulsed Drain Current[a]		I_{DM}	0.5	0.8	1	1			
Power Dissipation	T_A= 25°C	P_D	0.4	0.2	1.3	1.3	2	0.83	W
	T_A= 100°C		0.16	0.08	0.52	0.52	0.8		
Maximum Junction-to-Ambient		R_{thJA}	312.5	625	96	96	62.5	156	°C/W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	–55 to 150						°C

Notes
a. Pulse width limited by maximum junction temperature.
b. $t_p \leq 50$ µs.

Specifications[a] for 2N7000 and 2N7002

Parameter	Symbol	Test Conditions	Typ[b]	Limits				Unit
				2N7000		2N7002		
				Min	Max	Min	Max	
Static								
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 10 µA	70	60		60		V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 1 mA	2.1	0.8	3			
		V_{DS} = V_{GS}, I_D = 0.25 mA	2.0			1	2.5	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±15 V			±10			nA
		V_{DS} = 0 V, V_{GS} = ±20 V					±100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 48 V, V_{GS} = 0 V			1			µA
		T_C = 125°C			1000			
		V_{DS} = 60 V, V_{GS} = 0 V					1	
		T_C = 125°C					500	
On-State Drain Current[c]	$I_{D(on)}$	V_{DS} = 10 V, V_{GS} = 4.5 V	0.35	0.075				A
		V_{DS} = 7.5 V, V_{GS} = 10 V	1			0.5		
Drain-Source On-Resistance[c]	$r_{DS(on)}$	V_{GS} = 4.5 V, I_D = 0.075 A	4.5		5.3			Ω
		V_{GS} = 5 V, I_D = 0.05 A	3.2				7.5	
		T_C = 125°C	5.8				13.5	
		V_{GS} = 10 V, I_D = 0.5 A	2.4		5		7.5	
		T_J = 125°C	4.4		9		13.5	
Forward Transconductance[c]	g_{fs}	V_{DS} = 10 V, I_D = 0.2 A		100		80		mS
Common Source Output Conductance[c]	g_{os}	V_{DS} = 5 V, I_D = 0.05 A	0.5					
Dynamic								
Input Capacitance	C_{iss}	V_{DS} = 25 V, V_{GS} = 0 V f = 1 MHz	22		60		50	pF
Output Capacitance	C_{oss}		11		25		25	
Reverse Transfer Capacitance	C_{rss}		2		5		5	

Specifications[a] for 2N7000 and 2N7002

Parameter	Symbol	Test Conditions	Typ[b]	Limits 2N7000 Min	Limits 2N7000 Max	Limits 2N7002 Min	Limits 2N7002 Max	Unit
Switching[e]								
Turn-On Time	t_{ON}	V_{DD} = 15 V, R_L = 25 Ω I_D ≅ 0.5 A, V_{GEN} = 10 V R_G = 25 Ω	7		10			ns
Turn-Off Time	t_{OFF}		7		10			
Turn-On Time	t_{ON}	V_{DD} = 30 V, R_L = 150 Ω I_D ≅ 0.2 A, V_{GEN} = 10 V R_G = 25 Ω	7				20	
Turn-Off Time	t_{OFF}		11				20	

Notes
a. T_A = 25°C unless otherwise noted.d. VNBF06
b. For DESIGN AID ONLY, not subject to production testing.
c. Pulse test: PW ≤ 80 µs duty cycle ≤ 1%.
d. This parameter not registered with JEDEC.
e. Switching time is essentially independent of operating temperature.

Specifications[a] for VQ1000J/P and BS170

Parameter	Symbol	Test Conditions	Typ[b]	Limits VQ1000J/P Min	Limits VQ1000J/P Max	Limits BS170 Min	Limits BS170 Max	Unit
Static								
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 100 µA	70	60		60		V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 1 mA	2.1	0.8	2.5	0.8	3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±10 V			±100			nA
		T_J = 125°C			±500			
		V_{DS} = 0 V, V_{GS} = ±15 V					±10	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 25 V, V_{GS} = 0 V					0.5	µA
		V_{DS} = 48 V, V_{GS} = 0 V, T_J = 125°C			500			
		V_{DS} = 60 V, V_{GS} = 0 V			10			
On-State Drain Current[c]	$I_{D(on)}$	V_{DS} = 10 V, V_{GS} = 10 V	1	0.5				A
Drain-Source On-Resistance[c]	$r_{DS(on)}$	V_{GS} = 5 V, I_D = 0.2 A	4		7.5			Ω
		V_{GS} = 10 V, I_D = 0.2 A	2.3				5	
		V_{GS} = 10 V, I_D = 0.3 A	2.3		5.5			
		T_J = 125°C	4.2		7.6			
Forward Transconductance[c]	g_{fs}	V_{DS} = 10 V, I_D = 0.2 A				100		mS
		V_{DS} = 10 V, I_D = 0.5 A		100				
Common Source Output Conductance[c]	g_{os}	V_{DS} =5 V, I_D = 0.05 A	0.5					
Dynamic								
Input Capacitance	C_{iss}	V_{DS} =25 V, V_{GS} = 0 V f = 1 MHz	22		60		60	pF
Output Capacitance	C_{oss}		11		25			
Reverse Transfer Capacitance	C_{rss}		2		5			

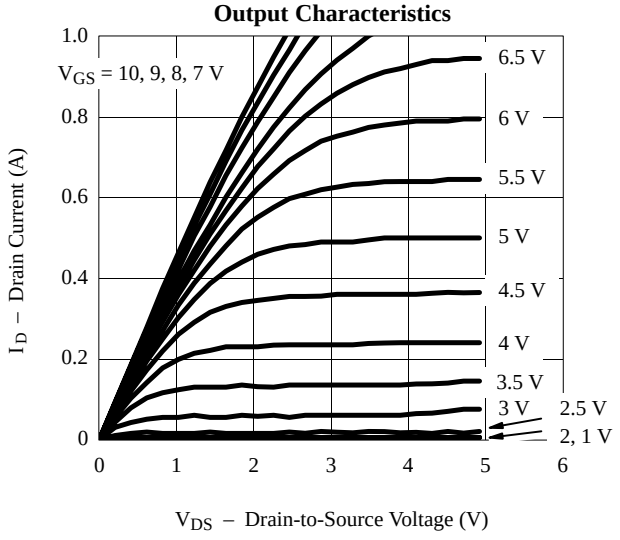
Specifications[a] for VQ1000J/P and BS170

Parameter	Symbol	Test Conditions	Typ[b]	Limits VQ1000J/P Min	Limits VQ1000J/P Max	Limits BS170 Min	Limits BS170 Max	Unit
Switching[d]								
Turn-On Time	t_{ON}	V_{DD} = 15 V, R_L = 23 Ω $I_D \cong$ 0.6 A, V_{GEN} = 10 V R_G = 25 Ω	7		10			ns
Turn-Off Time	t_{OFF}		7		10			
Turn-On Time	t_{ON}	V_{DD} = 25 V, R_L = 125 Ω $I_D \cong$ 0.2 A, V_{GEN} = 10 V R_G = 25 Ω	7				10	
Turn-Off Time	t_{OFF}		7				10	

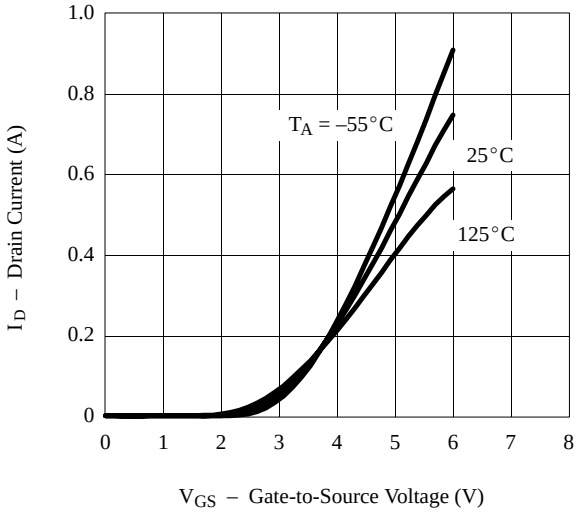
Notes
a. T_A = 25°C unless otherwise noted. VNBF06
b. For DESIGN AID ONLY, not subject to production testing.
c. Pulse test: PW ≤ 80 µs duty cycle ≤ 1%.
d. Switching time is essentially independent of operating temperature.

Typical Characteristics (25°C Unless Otherwise Noted)

Output Characteristics

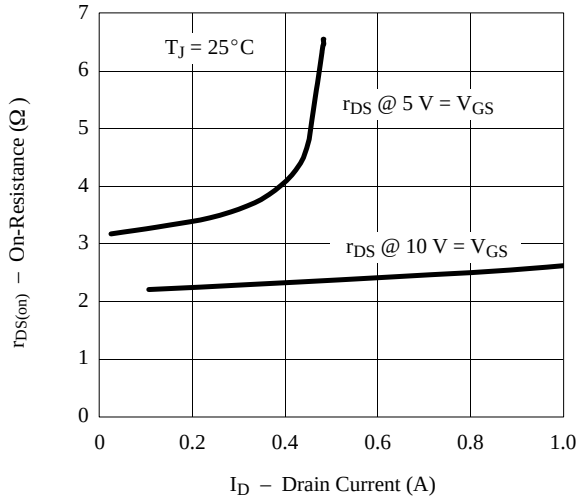


Transfer Characteristics

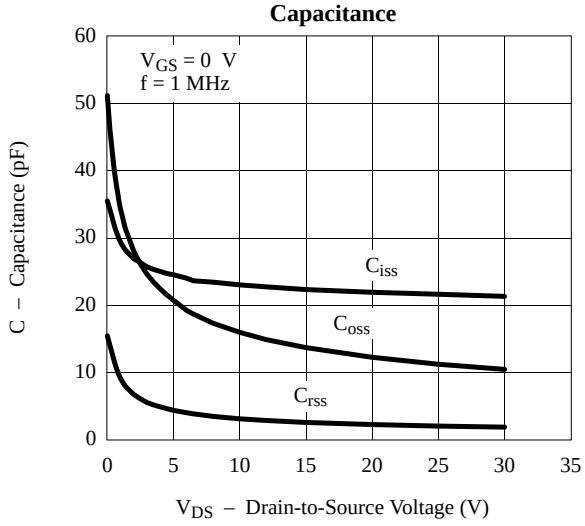


Typical Characteristics (25°C Unless Otherwise Noted)

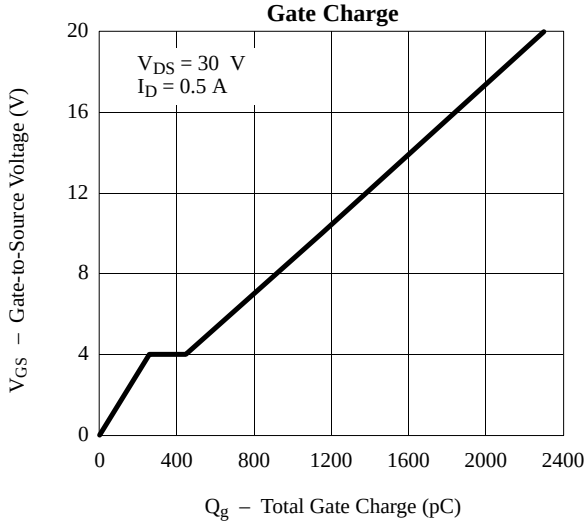
On-Resistance vs. Drain Current



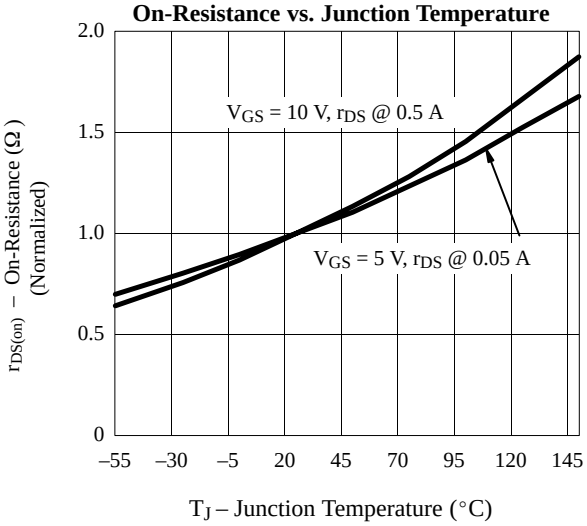
Capacitance



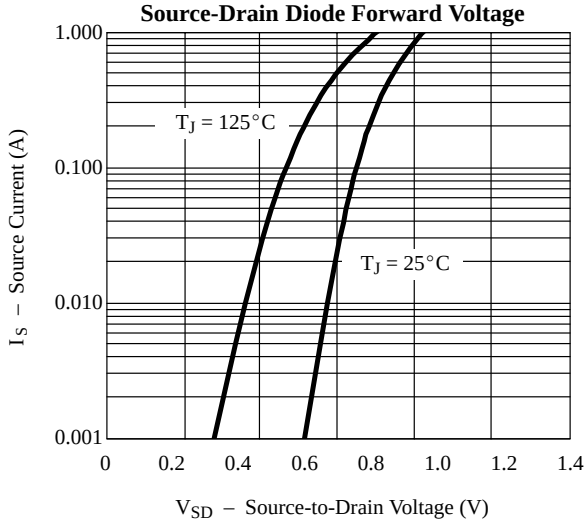
Gate Charge



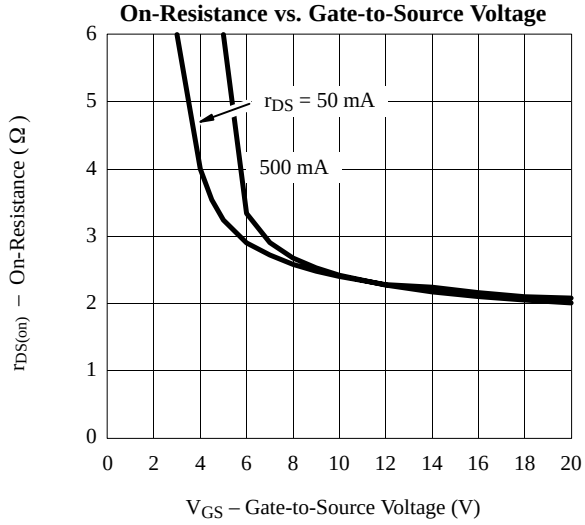
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

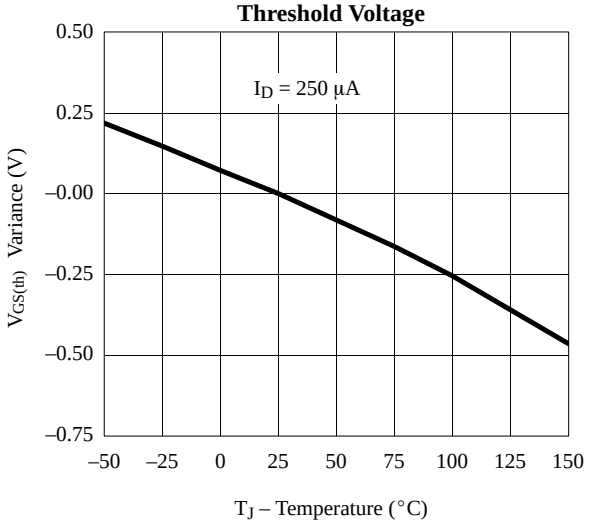


On-Resistance vs. Gate-to-Source Voltage



Typical Characteristics (25°C Unless Otherwise Noted)

Threshold Voltage



Normalized Effective Transient Thermal Impedance, Junction-to-Ambient (TO-226AA, BS170 Only)